

## **Description**

The SI2302-HXY uses advanced trench technology

to provide excellent RDS(ON), low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 20V I_{D} = 2.8A$ 

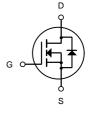
 $R_{DS(ON)} < 55 m\Omega @ V_{GS} = 4.5 V$ 

## **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
SI2302-HXY	SOT-23	A2SHB XXX YYYY	3000

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	20	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	2.8	A
Ірм	Drain Current-Pulsed (Note 1)	12	A
P <sub>D</sub>	Maximum Power Dissipation	0.9	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	139	°C/W



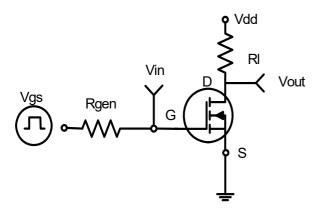
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	22	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.75	1.2	V
	$R_{DS(ON)} = \begin{cases} V_{GS}=2.5V, I_{D}=2A \\ V_{GS}=4.5V, I_{D}=2.8A \end{cases}$	V <sub>GS</sub> =2.5V, I <sub>D</sub> =2A	-	62	73	mΩ
Drain-Source On-State Resistance		-	43	55	mΩ	
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =3A	-	8	-	S
Input Capacitance	C <sub>lss</sub>		-	260	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	48	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	27	-	PF
Turn-on Delay Time	td(on)		-	2.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =3.3Ω	-	3.2	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V, $R_{GEN}$ =6 $\Omega$	-	21	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3	-	nS
Total Gate Charge	Qg		-	2.9	5	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =10V,I <sub>D</sub> =3A,	-	0.4	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =4.5V	-	0.6	-	nC
Diode Forward Voltage (Note 3)	VsD	V <sub>GS</sub> =0V,I <sub>S</sub> =3.3A	-	0.75	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3.3	Α

#### Notes:

- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



# **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 

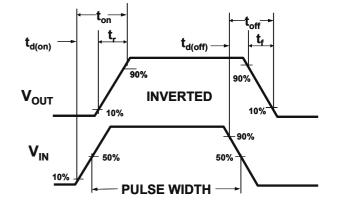
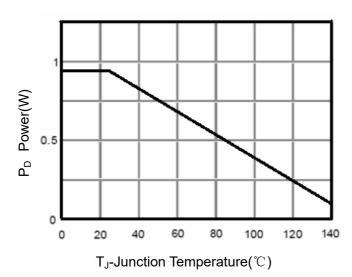
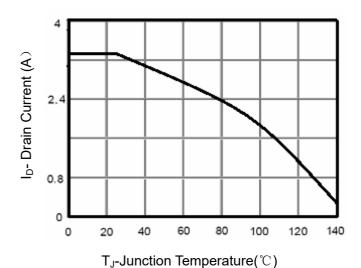


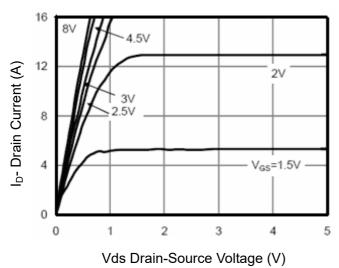
Figure 2:Switching Waveforms



**Figure 3 Power Dissipation** 



**Figure 4 Drain Current** 



**Figure 5 Output Characteristics** 

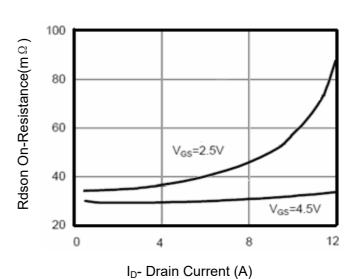
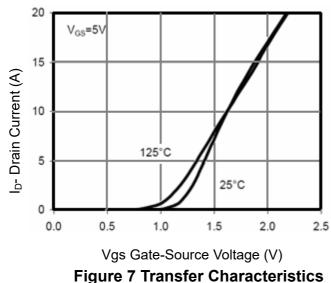
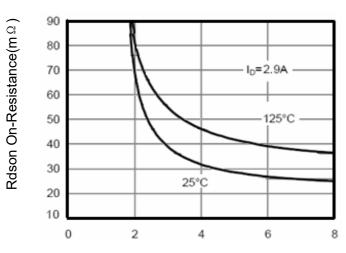


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs

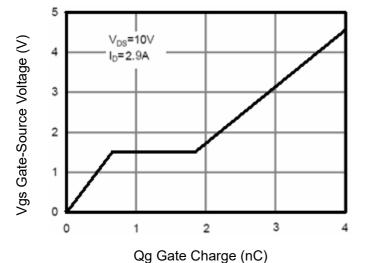


Figure 11 Gate Charge

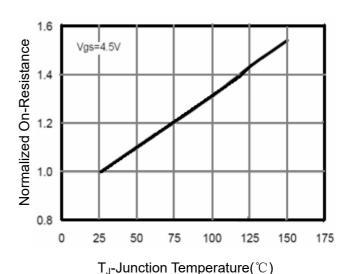
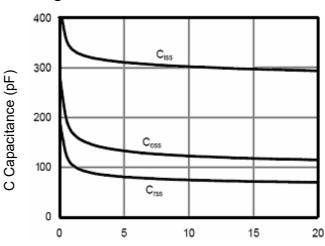
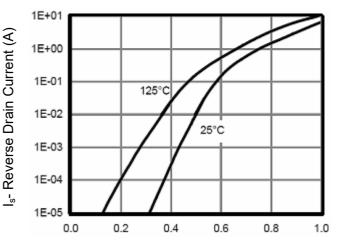


Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds

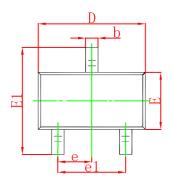


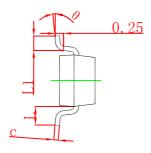
Vsd Source-Drain Voltage (V)

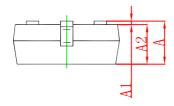
Figure 12 Source- Drain Diode Forward



# **SOT-23 Package Outline Dimensions**

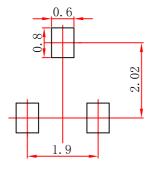






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



- Note:
  1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.

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